

TRENCHSTOP™ series

Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	600	V
DC collector current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ value limited by bondwire $T_c = 135^{\circ}\text{C}$	I_C	160.0 120.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	480.0	A
Turn off safe operating area $V_{CE} \leq 600\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$	-	480.0	A
Diode forward current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ $T_c = 124^{\circ}\text{C}$	I_F	160.0 120.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	480.0	A
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 400\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^{\circ}\text{C}$	t_{SC}	5	μs
Power dissipation $T_c = 25^{\circ}\text{C}$	P_{tot}	833.0	W
Operating junction temperature	T_{vj}	-40...+175	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55...+150	$^{\circ}\text{C}$
Soldering temperature, ¹⁾ wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R_{th} Characteristics						
IGBT thermal resistance, ²⁾ junction - case	$R_{th(j-c)}$		-	-	0.18	K/W
Diode thermal resistance, ²⁾ junction - case	$R_{th(j-c)}$		-	-	0.30	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

¹⁾ Package not recommended for surface mount application

²⁾ Thermal resistance of thermal grease $R_{th(c-s)}$ (case to heat sink) of more than 0.1K/W not included.

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Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}, I_C = 0.20\text{mA}$	600	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0\text{V}, I_C = 120.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	1.50 1.90	2.00 -	V
Diode forward voltage	V_F	$V_{GE} = 0\text{V}, I_F = 120.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	1.65 1.60	2.05 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 1.92\text{mA}, V_{CE} = V_{GE}$	4.1	4.9	5.7	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 600\text{V}, V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	- 3000	40 -	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20\text{V}, I_C = 120.0\text{A}$	-	75.0	-	S
Integrated gate resistor	r_G			none		Ω

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	7530	-	pF
Output capacitance	C_{oes}		-	446	-	
Reverse transfer capacitance	C_{res}		-	206	-	
Gate charge	Q_G	$V_{CC} = 480\text{V}, I_C = 120.0\text{A},$ $V_{GE} = 15\text{V}$	-	703.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH
Short circuit collector current Max. 1000 short circuits Time between short circuits: $\geq 1.0\text{s}$	$I_{C(SC)}$	$V_{GE} = 15.0\text{V}, V_{CC} \leq 400\text{V},$ $t_{SC} \leq 5\mu\text{s}$ $T_{vj} = 175^{\circ}\text{C}$	-	846	-	A

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 120.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 3.0\Omega, R_{G(off)} = 3.0\Omega,$ $L\sigma = 63\text{nH}, C\sigma = 31\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	33	-	ns
Rise time	t_r		-	43	-	ns
Turn-off delay time	$t_{d(off)}$		-	310	-	ns
Fall time	t_f		-	33	-	ns
Turn-on energy	E_{on}		-	4.10	-	mJ
Turn-off energy	E_{off}		-	2.80	-	mJ
Total switching energy	E_{ts}		-	6.90	-	mJ